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# FDMC86320

## N-Channel Power Trench<sup>®</sup> MOSFET 80 V, 22 A, 11.7 mΩ



### Features

- Max  $r_{DS(on)}$  = 11.7 mΩ at  $V_{GS} = 10$  V,  $I_D = 10.7$  A
- Max  $r_{DS(on)}$  = 16 mΩ at  $V_{GS} = 8$  V,  $I_D = 8.5$  A
- MSL1 robust package design
- 100% UIL Tested
- RoHS Compliant

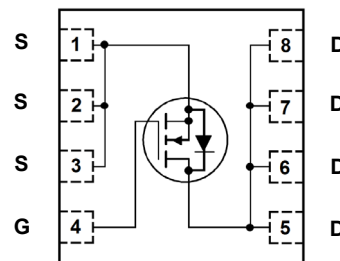
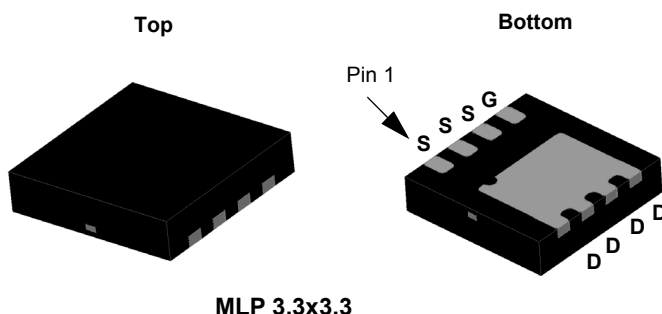


### General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$ , fast switching speed and body diode reverse recovery performance.

### Applications

- Primary DC-DC Switch
- Motor Bridge Switch
- Synchronous Rectifier



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter  | Ratings     | Units            |
|----------------|--|-------------|------------------|
| $V_{DS}$       | Drain to Source Voltage                              | 80          | V                |
| $V_{GS}$       | Gate to Source Voltage                               | $\pm 20$    | V                |
| $I_D$          | Drain Current -Continuous $T_C = 25^\circ\text{C}$   | 22          | A                |
|                | -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)       | 10.7        |                  |
|                | -Pulsed  | 50          |                  |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 3)               | 60          | mJ               |
| $P_D$          | Power Dissipation $T_C = 25^\circ\text{C}$           | 40          | W                |
|                | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a) | 2.3         |                  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range     | -55 to +150 | $^\circ\text{C}$ |

### Thermal Characteristics

|                 |   |     |                    |
|-----------------|---|-----|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case              | 3.1 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 53  |                    |

### Package Marking and Ordering Information

| Device Marking | Device    | Package  | Reel Size | Tape Width | Quantity   |
|----------------|-----------|----------|-----------|------------|------------|
| FDMC86320      | FDMC86320 | Power 33 | 13 "      | 12 mm      | 3000 units |

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

**Off Characteristics**

|                                      |   |   |    |    |           |                      |
|--------------------------------------|---|---|----|----|-----------|----------------------|
| $BV_{DSS}$                           | Drain to Source Breakdown Voltage         | $I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$           | 80 |    |           | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$ |    | 56 |           | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 64\ \text{V}$ , $V_{GS} = 0\ \text{V}$            |    |    | 1         | $\mu\text{A}$        |
| $I_{GSS}$                            | Gate to Source Leakage Current            | $V_{GS} = \pm 20\ \text{V}$ , $V_{DS} = 0\ \text{V}$        |    |    | $\pm 100$ | nA                   |

**On Characteristics**

|  |  |  |     |      |      |                      |
|--|--|--|-----|------|------|----------------------|
| $V_{GS(th)}$                           | Gate to Source Threshold Voltage                         | $V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$                                 | 2.4 | 3.5  | 4.5  | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$                  |     | -11  |      | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$                           | Static Drain to Source On Resistance                     | $V_{GS} = 10\ \text{V}$ , $I_D = 10.7\ \text{A}$                             |     | 9.7  | 11.7 | m $\Omega$           |
|  |  | $V_{GS} = 8\ \text{V}$ , $I_D = 8.5\ \text{A}$                               |     | 11.4 | 16   |                      |
|  |  | $V_{GS} = 10\ \text{V}$ , $I_D = 10.7\ \text{A}$ , $T_J = 125^\circ\text{C}$ |     | 15   | 18   |                      |
| $g_{FS}$                               | Forward Transconductance                                 | $V_{DS} = 10\ \text{V}$ , $I_D = 10.7\ \text{A}$                             |     | 20   |      | S                    |

**Dynamic Characteristics**

|           |                              |   |  |      |      |          |
|-----------|------------------------------|---|--|------|------|----------|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 40\ \text{V}$ , $V_{GS} = 0\ \text{V}$ ,<br>$f = 1\ \text{MHz}$ |  | 1985 | 2640 | pF       |
| $C_{oss}$ | Output Capacitance           |   |  | 353  | 469  | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance |   |  | 12   | 30   | pF       |
| $R_g$     | Gate Resistance              |   |  | 0.5  |      | $\Omega$ |

**Switching Characteristics**

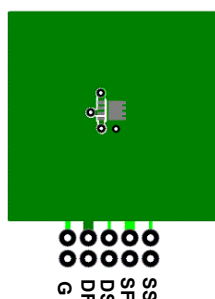
|              |                               |   |   |     |    |    |
|--------------|-------------------------------|---|---|-----|----|----|
| $t_{d(on)}$  | Turn-On Delay Time            | $V_{DD} = 40\ \text{V}$ , $I_D = 10.7\ \text{A}$ ,<br>$V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$ |   | 15  | 28 | ns |
| $t_r$        | Rise Time                     |   |   | 8   | 16 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time           |   |   | 20  | 35 | ns |
| $t_f$        | Fall Time                     |   |   | 5   | 10 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ to $10\ \text{V}$  | $V_{DD} = 40\ \text{V}$ ,<br>$I_D = 10.7\ \text{A}$ | 29  | 41 | nC |
| $Q_{g(TOT)}$ | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ to $8\ \text{V}$   |   | 24  | 34 | nC |
| $Q_{gs}$     | Total Gate Charge             |   |   | 10  |    | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge |   |   | 6.9 |    | nC |

**Drain-Source Diode Characteristics**

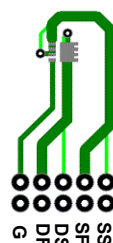
|          |                                       |  |  |      |     |    |
|----------|---------------------------------------|--|--|------|-----|----|
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS} = 0\ \text{V}$ , $I_S = 10.7\ \text{A}$ (Note 2)     |  | 0.84 | 1.3 | V  |
|          |                                       | $V_{GS} = 0\ \text{V}$ , $I_S = 2\ \text{A}$ (Note 2)        |  | 0.75 | 1.2 |    |
| $t_{rr}$ | Reverse Recovery Time                 | $I_F = 10.7\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$ |  | 38   | 61  | ns |
| $Q_{rr}$ | Reverse Recovery Charge               |  |  | 27   | 43  | nC |

## NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\ \text{in}^2$  pad 2 oz copper pad on a  $1.5\ \text{x}\ 1.5\ \text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $53^\circ\text{C/W}$  when mounted on a  $1\ \text{in}^2$  pad of 2 oz copper



b.  $125^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width  $< 300\ \mu\text{s}$ , Duty cycle  $< 2.0\%$ .

3. Starting  $T_J = 25^\circ\text{C}$ ; N-ch:  $L = 0.3\ \text{mH}$ ,  $I_{AS} = 20\ \text{A}$ ,  $V_{DD} = 72\ \text{V}$ ,  $V_{GS} = 10\ \text{V}$ .

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

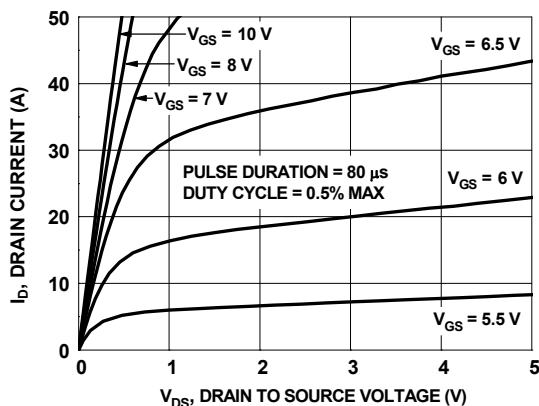


Figure 1. On Region Characteristics

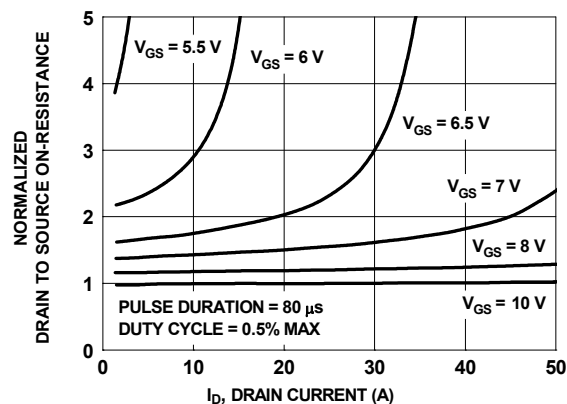


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

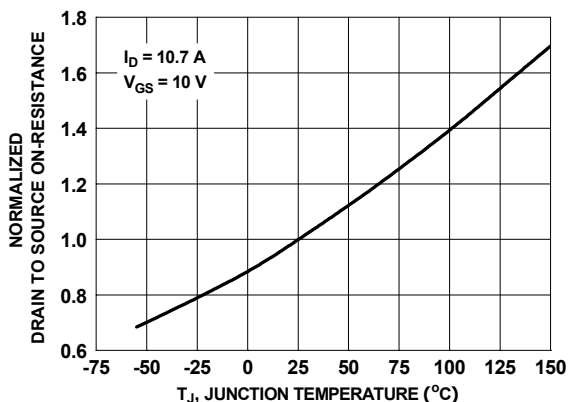


Figure 3. Normalized On Resistance vs. Junction Temperature

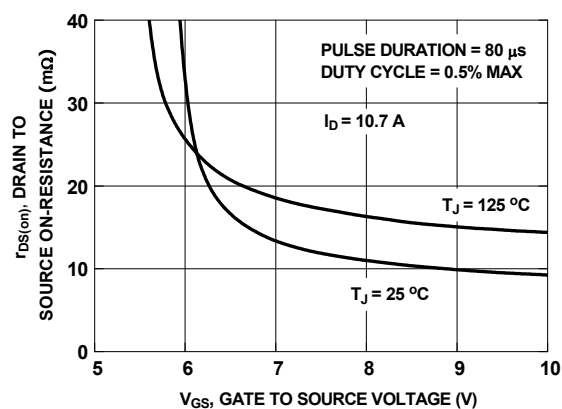


Figure 4. On-Resistance vs. Gate to Source Voltage

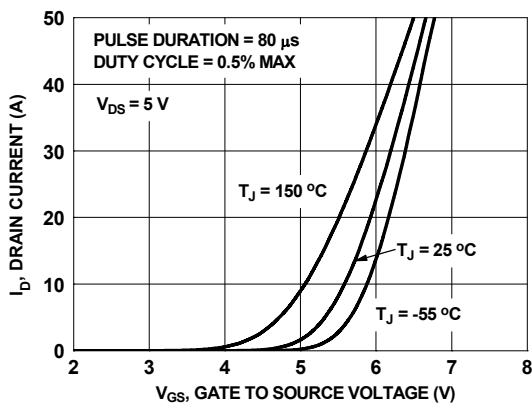


Figure 5. Transfer Characteristics

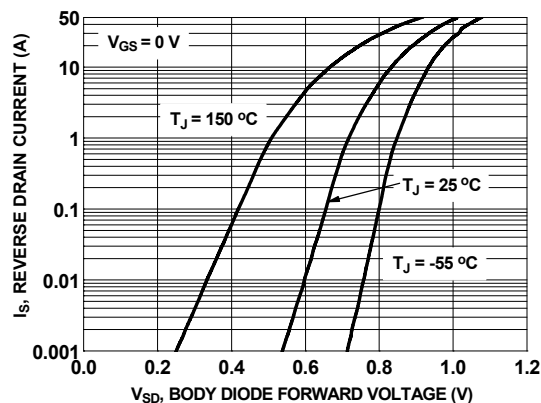


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

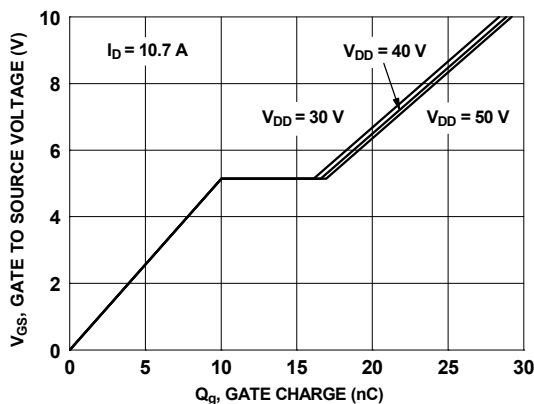


Figure 7. Gate Charge Characteristics

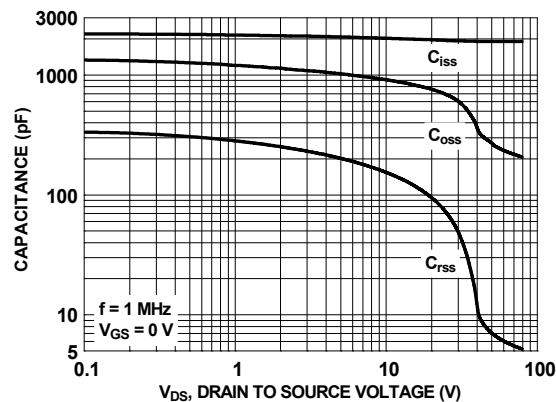


Figure 8. Capacitance vs. Drain to Source Voltage

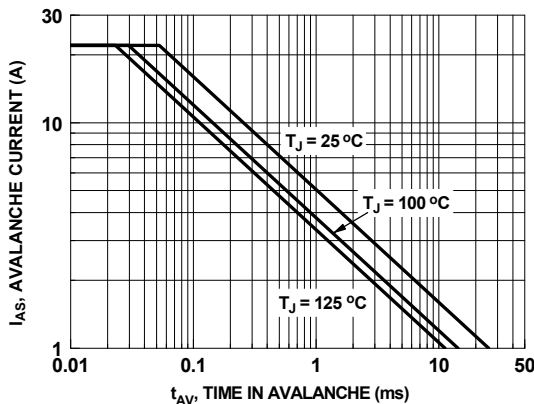


Figure 9. Unclamped Inductive Switching Capability

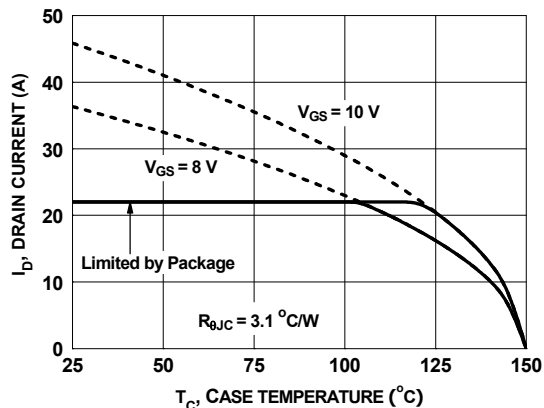


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

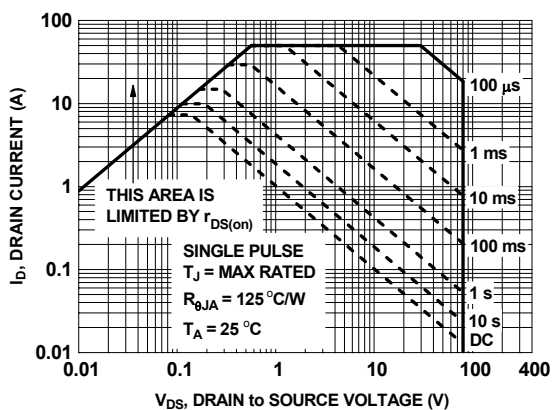


Figure 11. Forward Bias Safe Operating Area

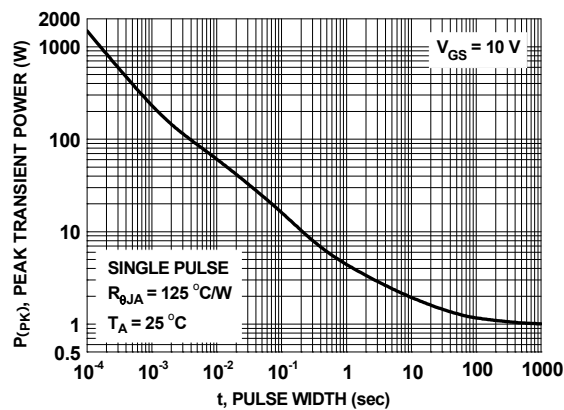


Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

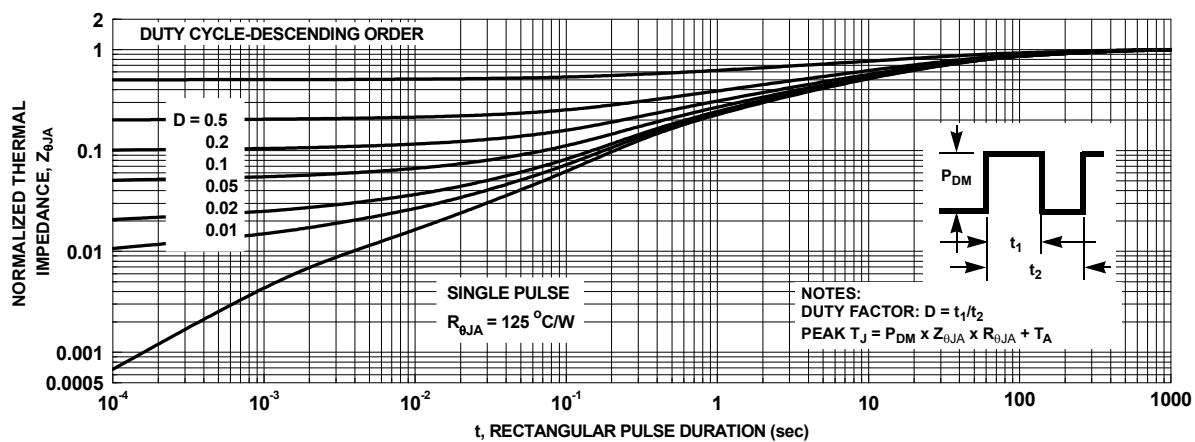
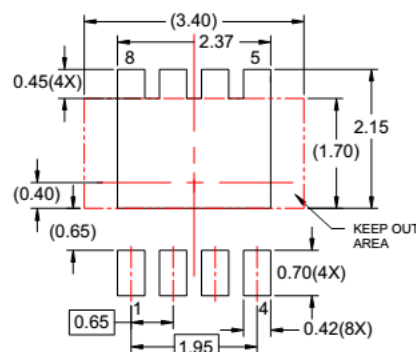
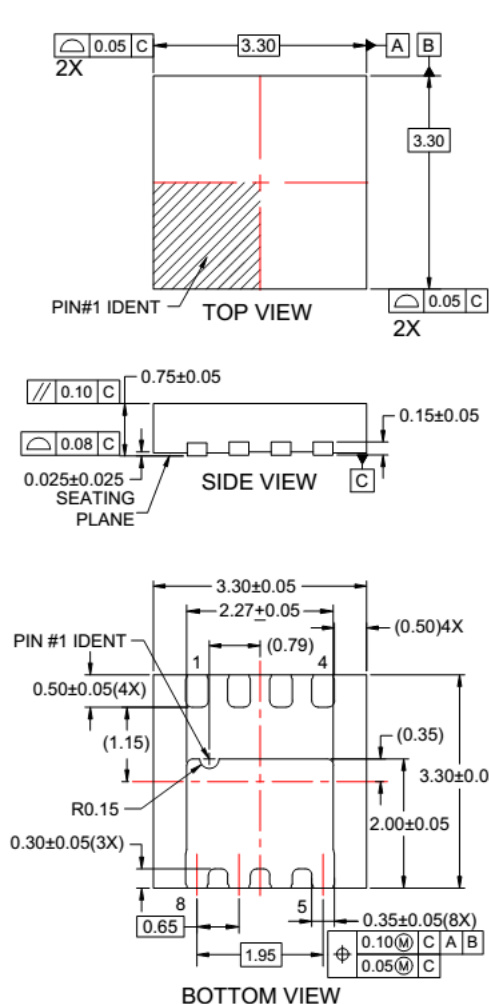


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

## Dimensional Outline and Pad Layout



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Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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